

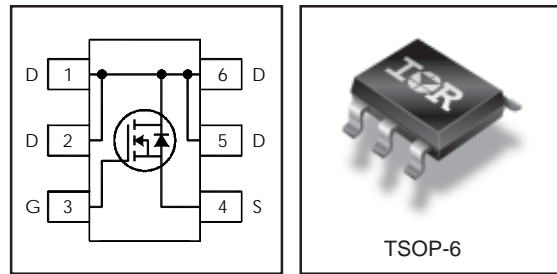
**Applications**

- High frequency DC-DC converters

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on)</sub> max</b>	<b>I<sub>D</sub></b>
<b>200V</b>	<b>2.2Ω</b>	<b>0.6A</b>

**Benefits**

- Low Gate to Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C<sub>OSS</sub> to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current
- Lead-Free



**Absolute Maximum Ratings**

	<b>Parameter</b>	<b>Max.</b>	<b>Units</b>
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	0.6	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	0.48	
I <sub>DM</sub>	Pulsed Drain Current ①	4.8	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Power Dissipation	2.0	W
	Linear Derating Factor	0.016	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ②	9.6	V/ns
T <sub>J</sub>	Operating Junction and	-55 to + 150	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

**Thermal Resistance**

<b>Symbol</b>	<b>Parameter</b>	<b>Typ.</b>	<b>Max.</b>	<b>Units</b>
R <sub>θJA</sub>	Junction-to-Ambient ④	—	62.5	°C/W

Notes ① through ⑥ are on page 8  
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## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	200	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.26	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA ③
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	2.2	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.36A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	3.0	—	5.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 160V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 30V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -30V

## Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

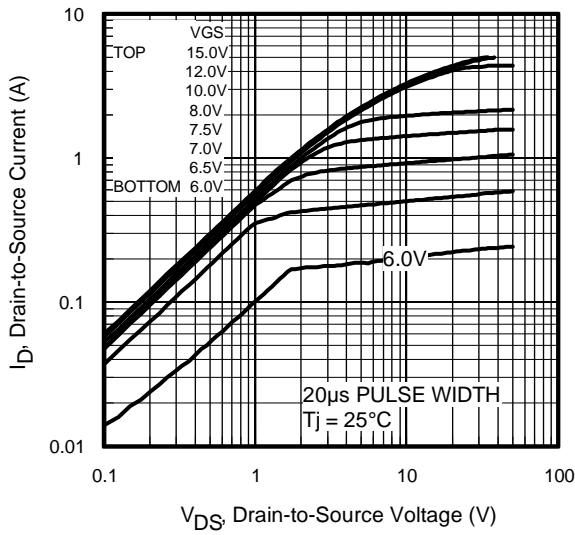
	Parameter	Min.	Typ.	Max.	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	0.44	—	—	S	V <sub>DS</sub> = 50V, I <sub>D</sub> = 0.36A
Q <sub>g</sub>	Total Gate Charge	—	3.9	—	nC	I <sub>D</sub> = 0.36A V <sub>DS</sub> = 160V V <sub>GS</sub> = 10V
Q <sub>gs</sub>	Gate-to-Source Charge	—	0.8	—		
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	2.2	—		
t <sub>d(on)</sub>	Turn-On Delay Time	—	6.5	—	ns	V <sub>DD</sub> = 100V I <sub>D</sub> = 0.36A R <sub>G</sub> = 53Ω V <sub>GS</sub> = 10V ③
t <sub>r</sub>	Rise Time	—	8.0	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	8.8	—		
t <sub>f</sub>	Fall Time	—	19	—		
C <sub>iss</sub>	Input Capacitance	—	88	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	18	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	6.3	—		
C <sub>oss</sub>	Output Capacitance	—	102	—		
C <sub>oss</sub>	Output Capacitance	—	8.4	—		
C <sub>oss eff.</sub>	Effective Output Capacitance	—	26	—		

## Avalanche Characteristics

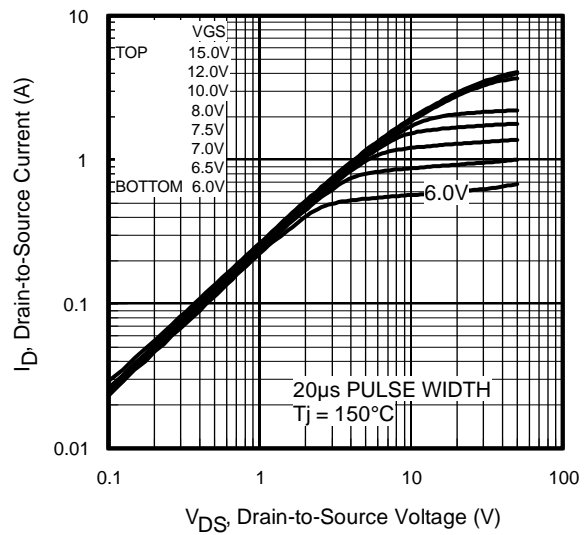
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	9.9	mJ
I <sub>AR</sub>	Avalanche Current①	—	0.6	A

## Diode Characteristics

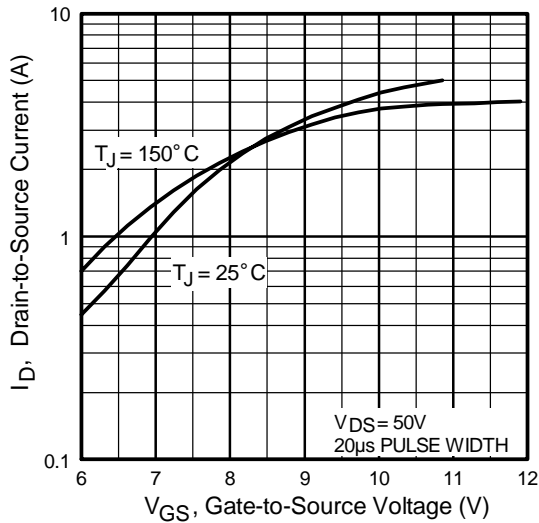
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	1.8	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	4.8		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 0.36A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	45	—	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 0.36A
Q <sub>rr</sub>	Reverse Recovery Charge	—	54	—	nC	di/dt = 100A/μs ③



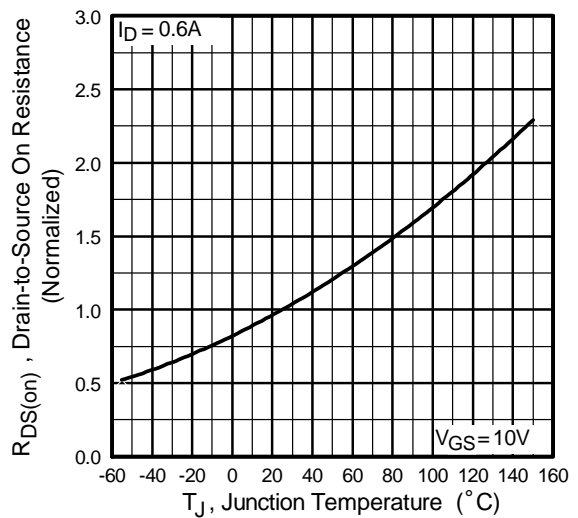
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

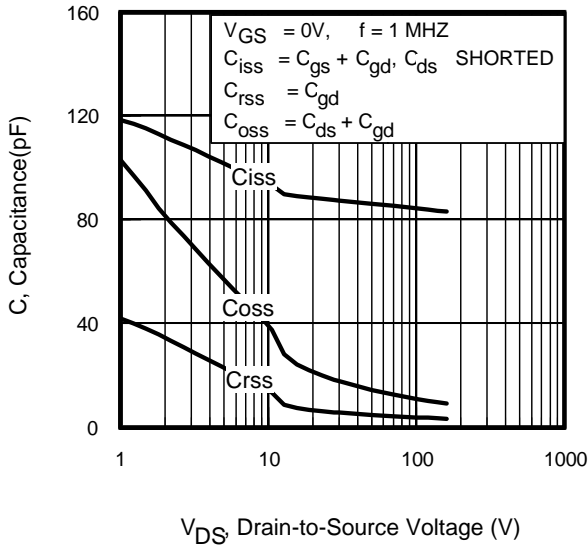


**Fig 3.** Typical Transfer Characteristics

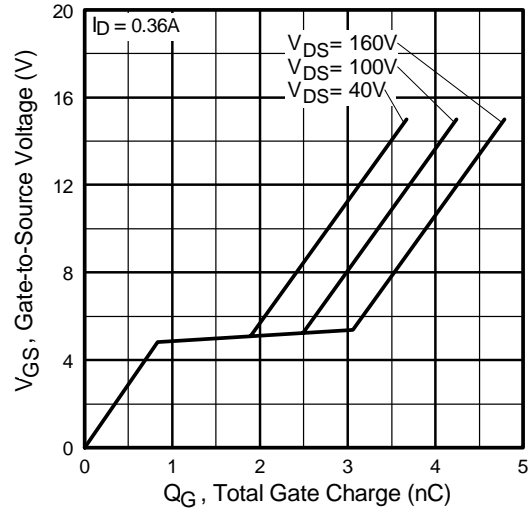


**Fig 4.** Normalized On-Resistance Vs. Temperature

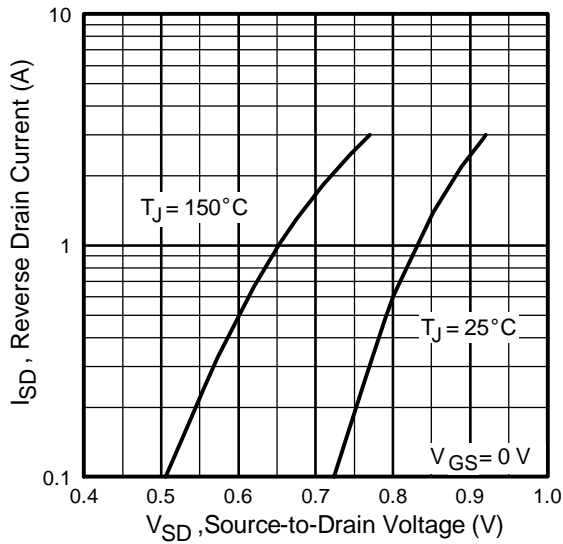
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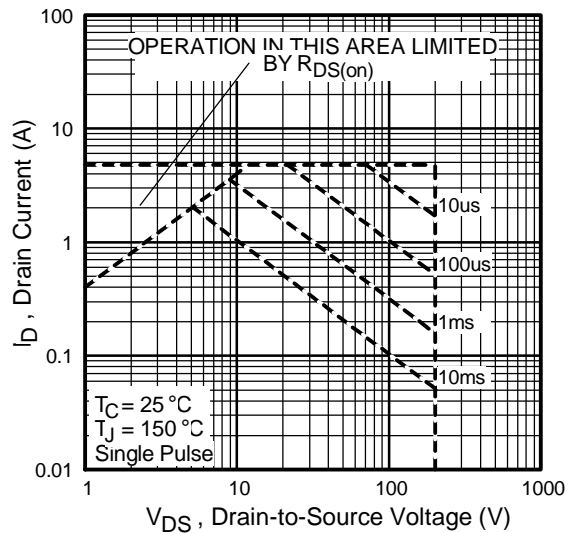
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



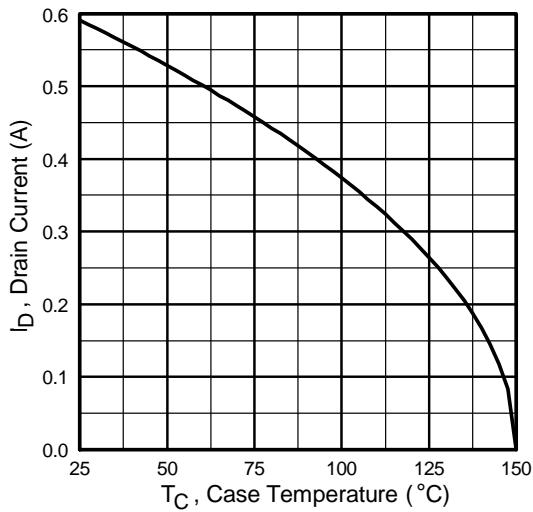
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



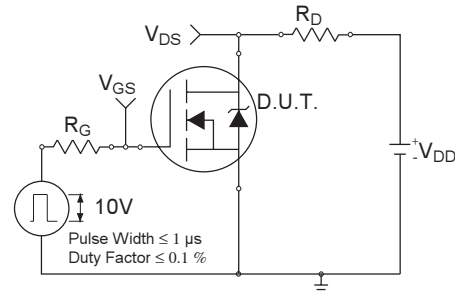
**Fig 7.** Typical Source-Drain Diode Forward Voltage



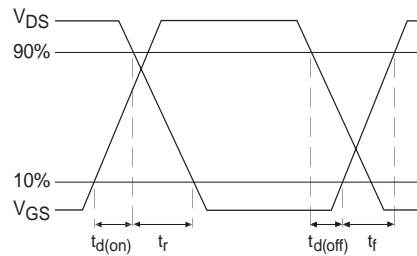
**Fig 8.** Maximum Safe Operating Area



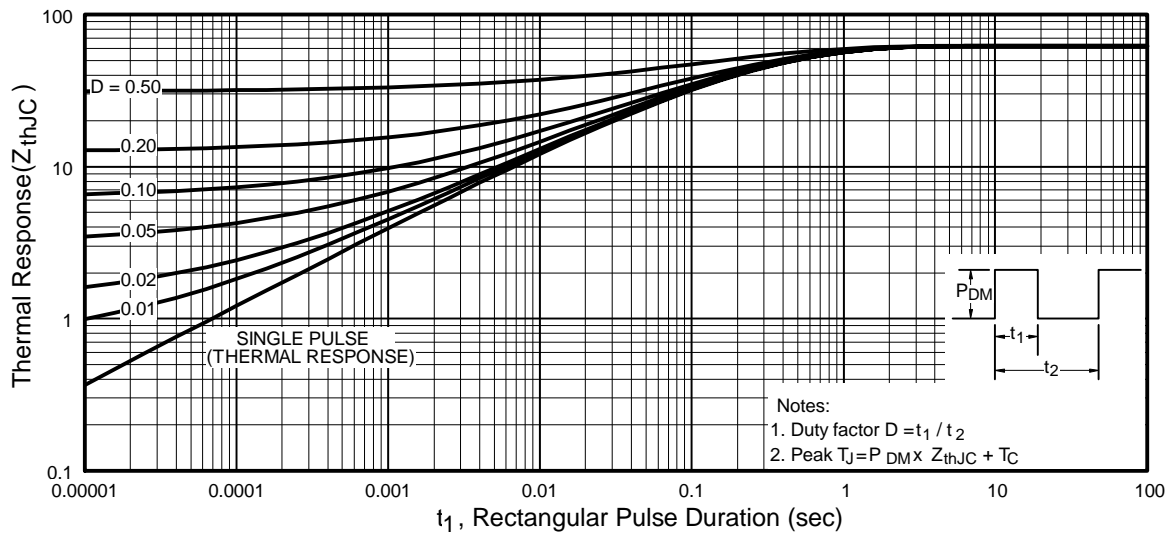
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



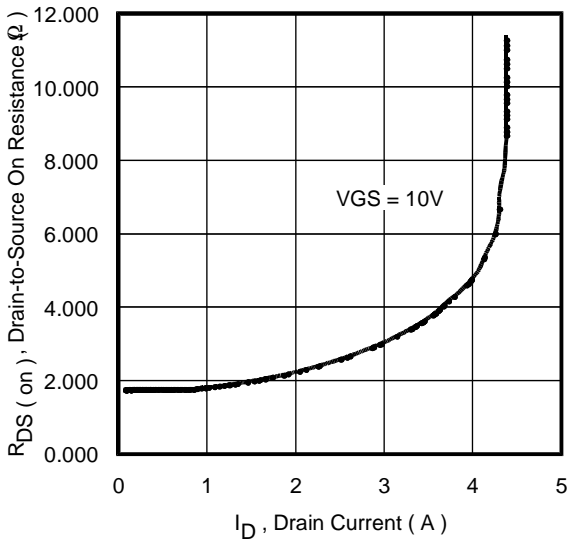
**Fig 10b.** Switching Time Waveforms



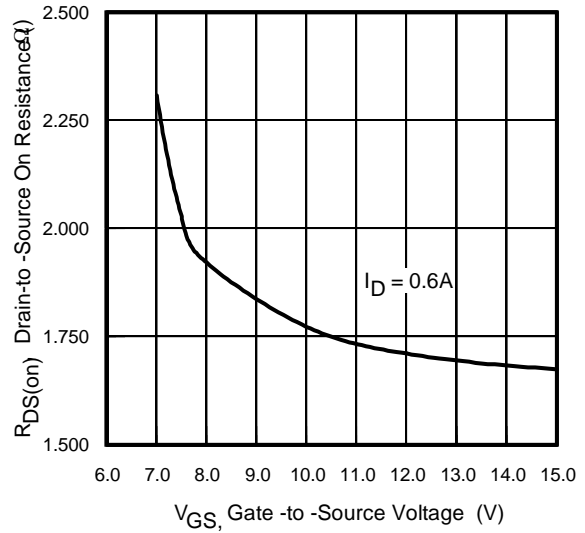
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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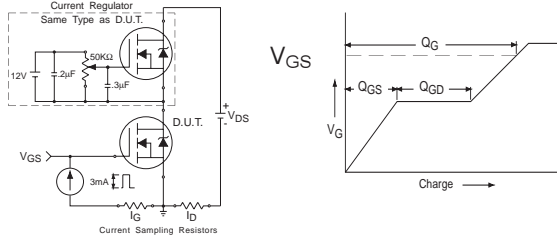
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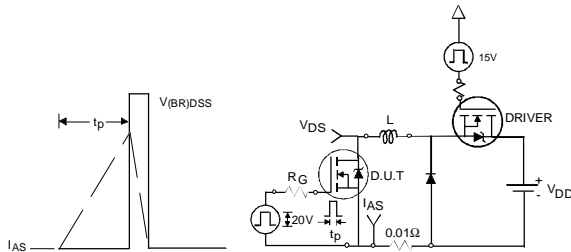
**Fig 12.** On-Resistance Vs. Drain Current



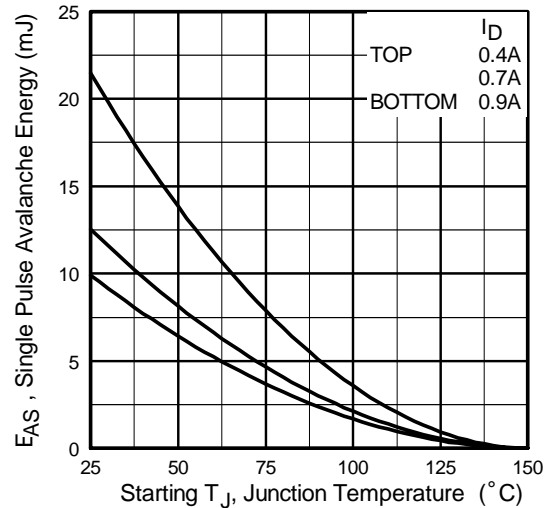
**Fig 13.** On-Resistance Vs. Gate Voltage



**Fig 14a&b.** Basic Gate Charge Test Circuit and Waveform

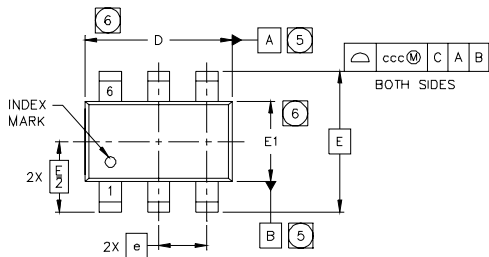


**Fig 15a&b.** Unclamped Inductive Test circuit and Waveforms

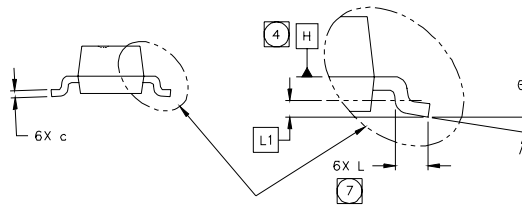
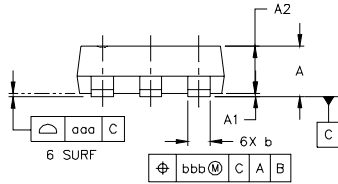


**Fig 15c.** Maximum Avalanche Energy Vs. Drain Current

## TSOP-6 Package Outline

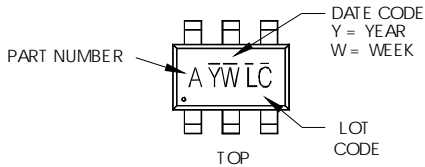


SYMBOL	MO-193AA DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	.0433
A1	0.01	---	0.10	.0004	---	.0039
A2	0.80	0.90	1.00	.0315	.0354	.0393
b	0.25	---	0.50	.0099	---	.0196
c	0.10	---	0.26	.004	---	.010
D	2.90	3.00	3.10	.115	.118	.122
E	2.75 BSC			.108 BSC		
E1	1.30	1.50	1.70	.052	.059	.066
e	1.00 BSC			.039 BSC		
L	0.20	0.40	0.60	.0079	.0157	.0236
L1	0.30 BSC			.0118 BSC		
θ	0°	---	8°	0°	---	8°
aaa	0.10			.004		
bbb	0.15			.006		
ccc	0.25			.010		



## TSOP-6 Part Marking Information

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

- A = SI3443DV
- B = IRF 5800
- C = IRF 5850
- D = IRF 5851
- E = IRF 5852
- F = IRF 5801
- I = IRF 5805
- J = IRF 5806
- K = IRF 5810
- L = IRF 5804
- M = IRF 5803
- N = IRF 5802

Note: A line above the work week (as shown here) indicates Lead-Free.

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
2006	6		
2007	7		
2008	8		
2009	9		
2010	0	24	X
		25	Y
		26	Z

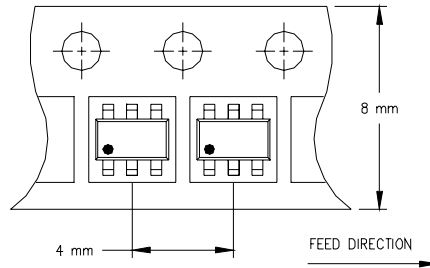
W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
2006	F		
2007	G		
2008	H		
2009	J		
2010	K	50	X
		51	Y
		52	Z

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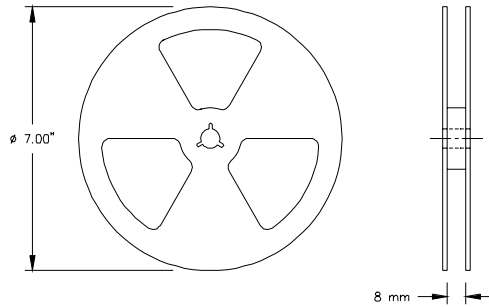
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## TSOP-6 Tape & Reel Information



NOTES:

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 27\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 0.36\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1 inch square copper board,  $t < 10\text{sec}$ .
- ⑤  $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥  $I_{SD} \leq 0.36\text{A}$ ,  $di/dt \leq 93\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 150^\circ\text{C}$ .

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualification Standards can be found on IR's Web site.

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TAC Fax: (310) 252-7903

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